

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims**

**Claim 1 (Previously Presented)**

A method for forming an adhesion between dielectric layers, the method comprising:  
providing a first dielectric layer; and  
in-situ forming a second dielectric layer having a first portion on said first dielectric layer and a second portion on said first portion, wherein said first portion has a first dielectric constant higher than said second portion has and said first portion comprises carbon.

**Claim 2 (Original)**

The method according to claim 1, wherein said first dielectric layer has a second dielectric constant which is higher than said second portion.

**Claim 3 (Original)**

The method according to claim 1, wherein the in-situ forming step having at least a process condition for forming said first portion and said second portion.

**Claim 4 (Original)**

The method according to claim 3, wherein the in-situ forming step having said process condition comprises:

executing a chemical vapor deposition having a first bias; and  
executing said chemical vapor deposition having a second bias, wherein said first bias is higher than said second bias.

**Claim 5 (Original)**

The method according to claim 3, wherein the in-situ forming step having said process condition comprises:

executing a chemical vapor deposition having a first HFRF for forming said first portion; and

executing said chemical vapor deposition having a second HFRF, wherein said first HFRF is higher than said second HFRF.

**Claim 6 (Original)**

The method according to claim 3, wherein the in-situ forming step having said process condition comprises:

executing a chemical vapor deposition having a first precursor for forming said first portion; and

executing said chemical vapor deposition having a second precursor, wherein the amount of said first precursor is less than the amount of said second precursor.

**Claim 7 (Original)**

The method according to claim 1, wherein the in-situ forming step comprises plasma enhanced chemical vapor deposition (PECVD).

**Claim 8 (Previously Presented)**

A method for forming an adhesion between dielectric layers, the method comprising:  
providing a first dielectric layer; and

in-situ forming a second dielectric layer having a first portion on said first dielectric layer and a second portion on said first portion, wherein said first portion has a hardness higher than said second portion has and said first portion comprises carbon.

**Claim 9 (Original)**

The method according to claim 8, wherein said first dielectric layer has a dielectric constant which is higher than said second dielectric layer.

**Claim 10 (Original)**

The method according to claim 8, wherein the in-situ forming step at least comprises:  
executing a chemical vapor deposition having a first bias for forming said first portion; and  
executing said chemical vapor deposition having a second bias for forming said second portion, wherein said first bias is higher than said second bias.

**Claim 11 (Previously Presented)**

The method according to claim 8, wherein the in-situ forming step at least comprises: executing a chemical vapor deposition having a first HFRF for forming said first portion; and executing said chemical vapor deposition having a second HFRF for forming said second portion, wherein said first HFRF is higher than said second HFRF.

**Claim 12 (Cancelled)**

**Claim 13 (Previously Presented)**

The method according to claim 8, wherein the in-situ forming step comprises: executing a chemical vapor deposition having a first process condition; and executing said chemical vapor deposition having a second process condition, wherein said second process condition forming said second portion having a dielectric constant smaller than said first process condition forming said first portion.

**Claim 14 (Original)**

The method according to claim 13, wherein said executing said chemical vapor deposition is plasma enhanced chemical vapor deposition (PECVD).

**Claim 15 (Previously Presented)**

An structure of enhanced-inter-adhesion dielectric layers, the structure comprising:  
a first dielectric layer; and  
a second dielectric layer having a first portion on said first dielectric layer and a second portion on said first portion, wherein said first portion has a first dielectric constant around 2.8 to 3.5 higher than said second portion and said first portion comprises carbon.

**Claim 16 (Original)**

The structure according to claim 15, wherein said first dielectric layer is silicon nitride (SiN).

**Claim 17 (Original)**

The structure according to claim 15, wherein said first dielectric layer is silicon carbide (SiC).

**Claim 18 (Original)**

The structure according to claim 15, wherein said second portion has a second dielectric constant around 1.1 to 3.